

Correction

In the version of the News & Views article 'Spin transistors: Closer to an all-electric device' originally published (*Nature Nanotech.* **10**, 21-22; 2015), the semiconductor heterostructure 'AlGaAs/GaAs' should have been 'InGaAs/InAlAs'. Corrected in the online versions after print 27 February 2015.